

UT30N06

POWER MOSFET

30A, 60V N-CHANNEL
POWER MOSFET

■ DESCRIPTION

The UTC **UT30N06** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$ and high switching speed.

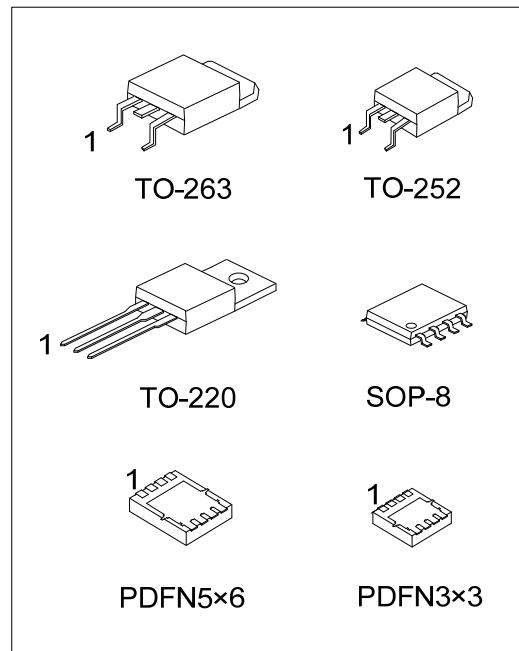
The UTC **UT30N06** is suitable for all commercial-industrial applications at power dissipation levels to approximately 50 watts, etc.

■ FEATURES

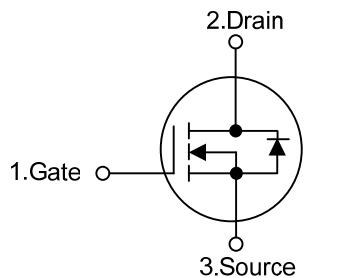
* $R_{DS(ON)} \leq 25 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=15\text{A}$

$R_{DS(ON)} \leq 35 \text{ m}\Omega @ V_{GS}=4.5\text{V}, I_D=15\text{A}$

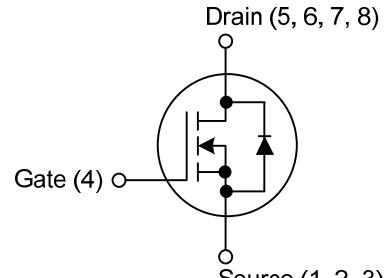
* High Switching Speed



■ SYMBOL



TO-220 / TO-252 / TO-263



SOP-8/PDFN3x3/PDFN5x6

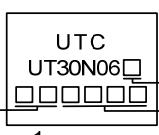
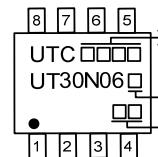
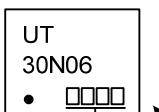
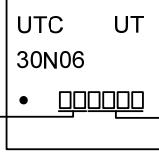
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UT30N06L-TA3-T	UT30N06G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
UT30N06L-TN3-R	UT30N06G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UT30N06L-TQ2-T	UT30N06G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
UT30N06L-TQ2-R	UT30N06G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
UT30N06L-S08-R	UT30N06G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel
UT30N06L-P3030-R	UT30N06G-P3030-R	PDFN3x3	S	S	S	G	D	D	D	D	Tape Reel
UT30N06L-P5060-R	UT30N06G-P5060-R	PDFN5x6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT30N06G-TA3-T	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel, T: Tube (2) TA3: TO-220, TN3: TO-252, TQ2: TO-263, S08: SOP-8, P3030: PDFN3x3, P5060: PDFN5x6 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

TO-220 / TO-252 / TO-263	SOP-8
 Lot Code ← 1 L: Lead Free G: Halogen Free	 Date Code L: Lead Free G: Halogen Free Lot Code →
PDFN3×3	PDFN5×6
 • Date Code	 Lot Code ← Date Code →

■ ABSOLUTE MAXIMUM RATING ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	30	A
	Pulsed (Note 2)	I_{DM}	60	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	26.9	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.26	V/ns
Power Dissipation	TO-220/TO-263	P_D	94	W
	TO-252		50	W
	SOP-8		1.7	W
	PDFN3x3		22	W
	PDFN5x6		25	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 0.1mH, $I_{AS} = 23.2\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD} \leq 10\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-263	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-252		110	$^\circ\text{C/W}$
	SOP-8		125	$^\circ\text{C/W}$
	PDFN3x3		60	$^\circ\text{C/W}$
	PDFN5x6		65	$^\circ\text{C/W}$
Junction to Case	TO-220/TO-263	θ_{JC}	1.5	$^\circ\text{C/W}$
	TO-252		2.5 (Note)	$^\circ\text{C/W}$
	SOP-8		33.7 (Note)	$^\circ\text{C/W}$
	PDFN3x3		5.5 (Note)	$^\circ\text{C/W}$
	PDFN5x6		4.9 (Note)	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

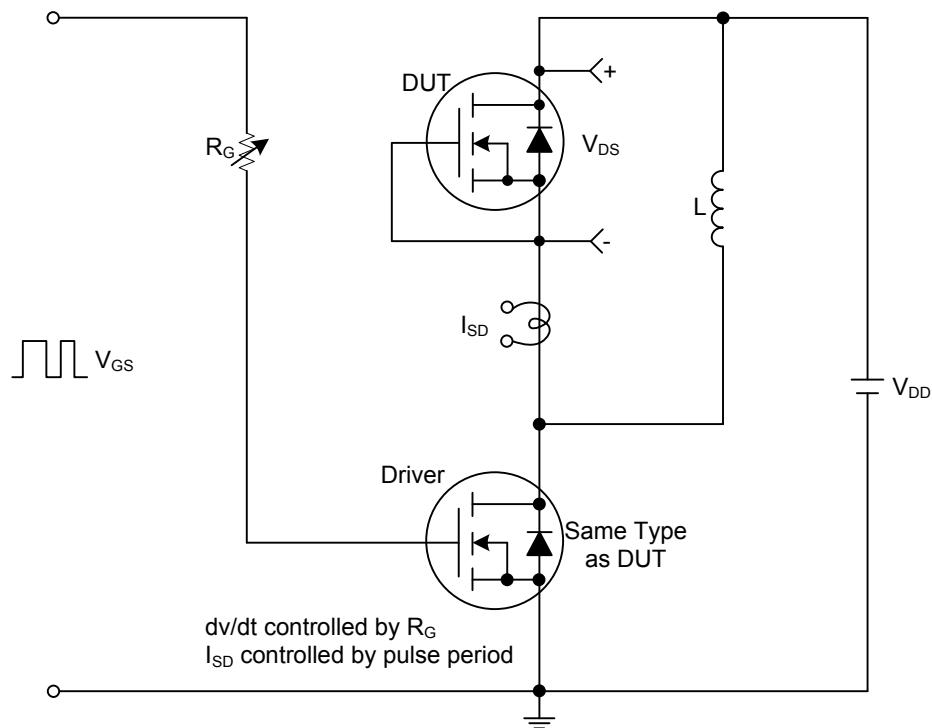
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{\text{GS}}=0\text{V}$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$			1	μA
Gate-Source Leakage Current	Forward	$V_{\text{GS}}=+20\text{V}, V_{\text{DS}}=0\text{V}$			+100	nA
	Reverse	$V_{\text{GS}}=-20\text{V}, V_{\text{DS}}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	1.0		3.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_D=15\text{A}$			25	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_D=15\text{A}$			35	$\text{m}\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=25\text{V}, f=1.0\text{MHz}$		1020		pF
Output Capacitance	C_{OSS}			118		pF
Reverse Transfer Capacitance	C_{RSS}			101		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{\text{DS}}=48\text{V}, V_{\text{GS}}=10\text{V}, I_D=30\text{A}, I_G=1\text{mA}$ (Note 1, 2)		29		nC
Gate to Source Charge	Q_{GS}			1.2		nC
Gate to Drain Charge	Q_{GD}			5.4		nC
Turn-on Delay Time (Note 1)	$t_{\text{D}(\text{ON})}$	$V_{\text{DD}}=30\text{V}, V_{\text{GS}}=10\text{V}, I_D=30\text{A}, R_G=3\Omega$ (Note 1, 2)		4.8		ns
Rise Time	t_R			16.6		ns
Turn-off Delay Time	$t_{\text{D}(\text{OFF})}$			28		ns
Fall-Time	t_F			19		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				30	A
Maximum Body-Diode Pulsed Current	I_{SM}				60	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=30\text{A}, V_{\text{GS}}=0\text{V}$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=30\text{A}, V_{\text{GS}}=0\text{V}, dI_F/dt = 100\text{A}/\mu\text{s}$		32		ns
Reverse Recovery Charge	Q_{rr}			58		nC

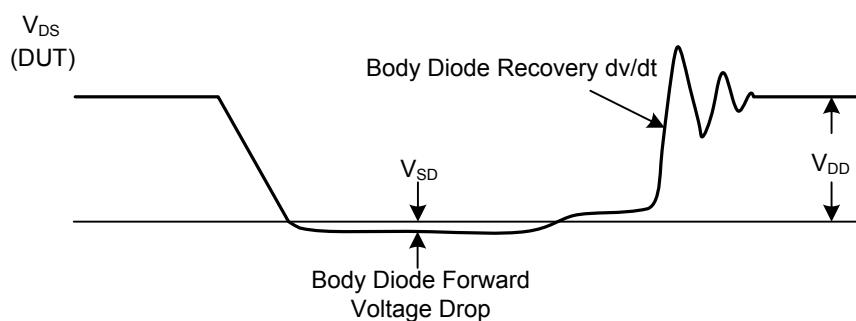
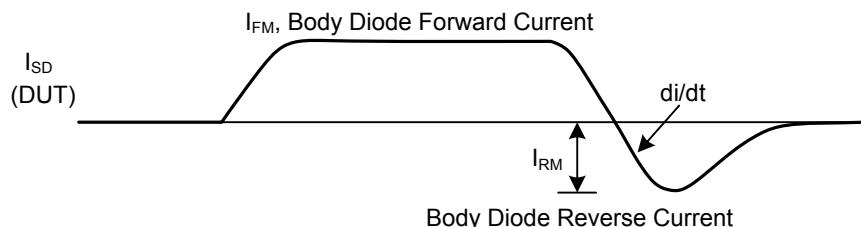
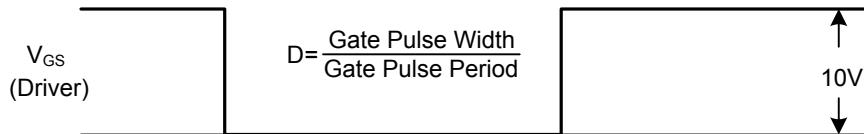
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS



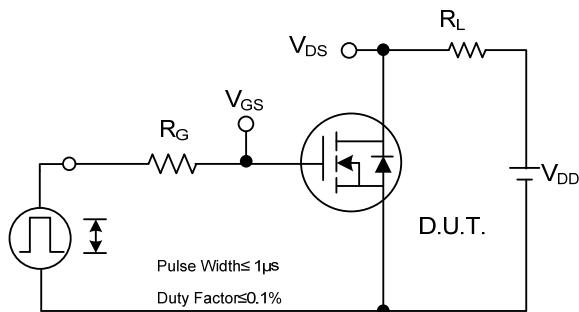
Peak Diode Recovery dV/dt Test Circuit



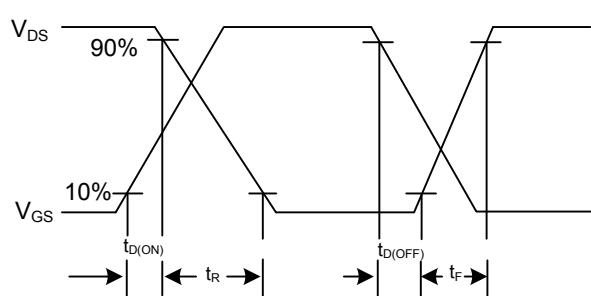
Peak Diode Recovery dV/dt Test Circuit and Waveforms

Peak Diode Recovery dV/dt Waveforms

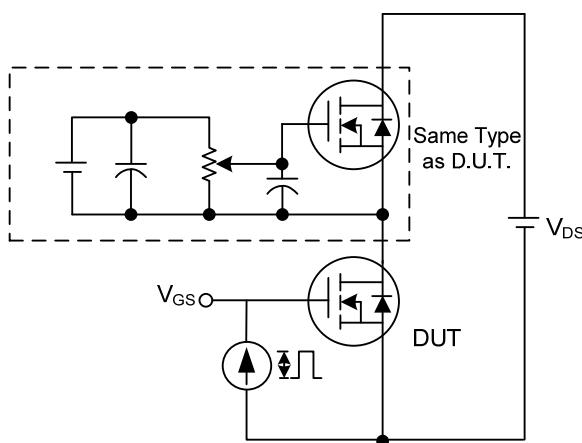
■ TEST CIRCUITS AND WAVEFORMS



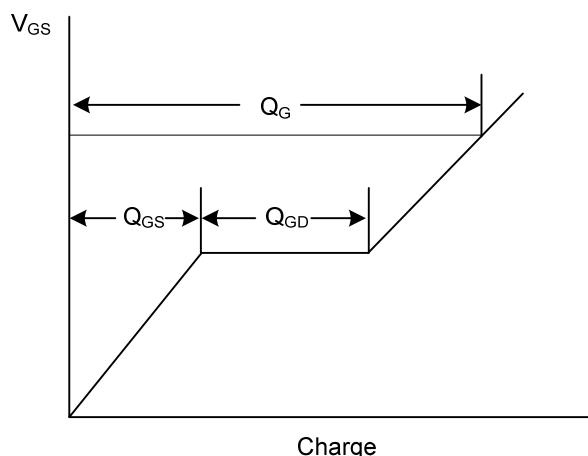
Switching Test Circuit



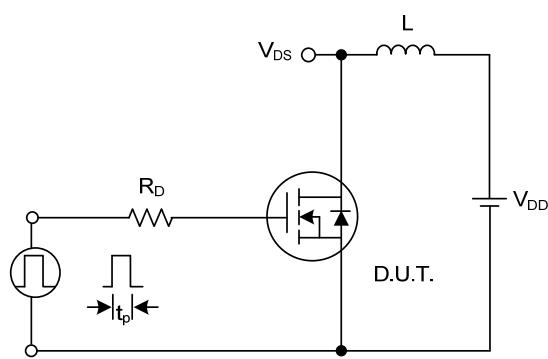
Switching Waveforms



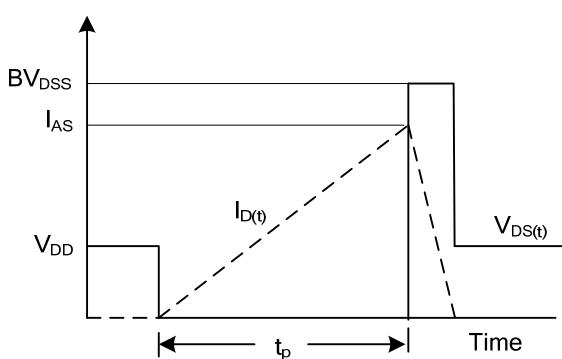
Gate Charge Test Circuit



Gate Charge Waveform

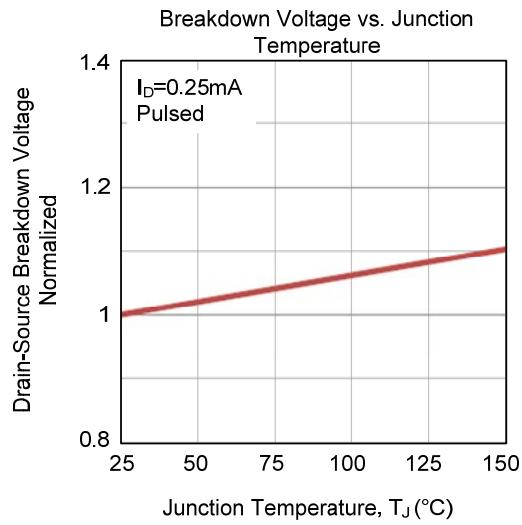
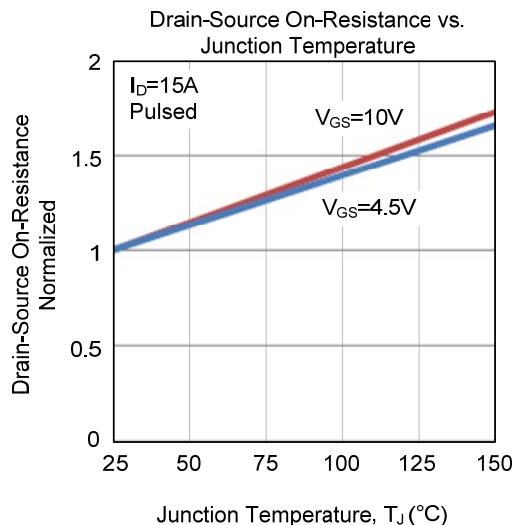
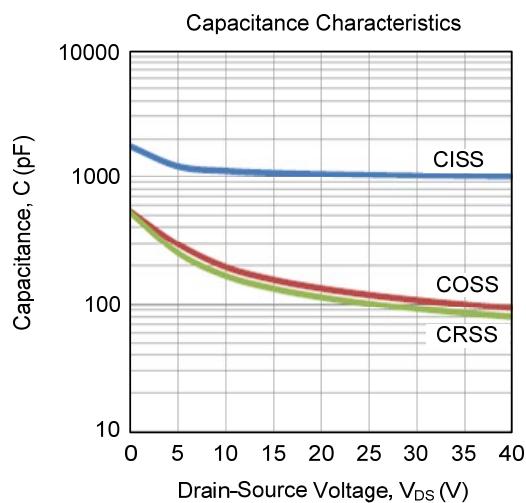
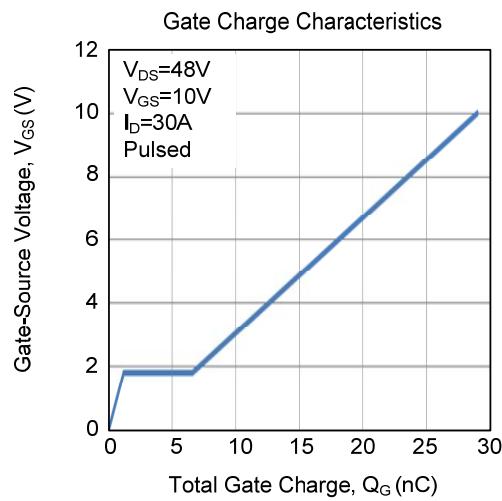
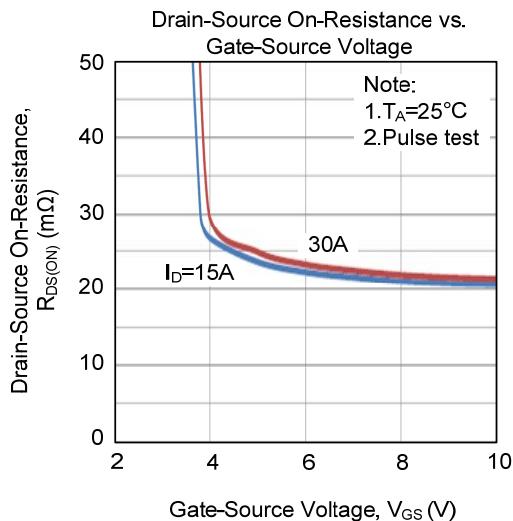
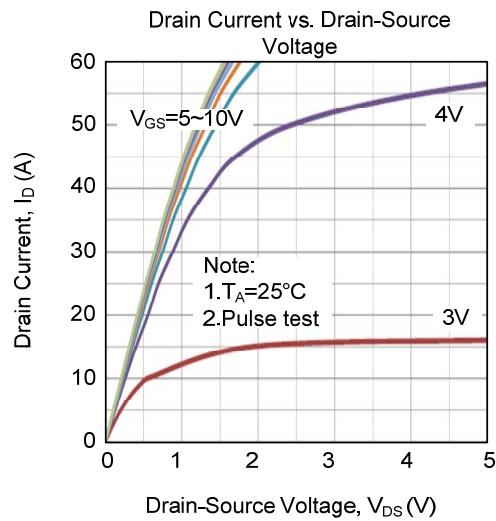


Unclamped Inductive Switching Test Circuit

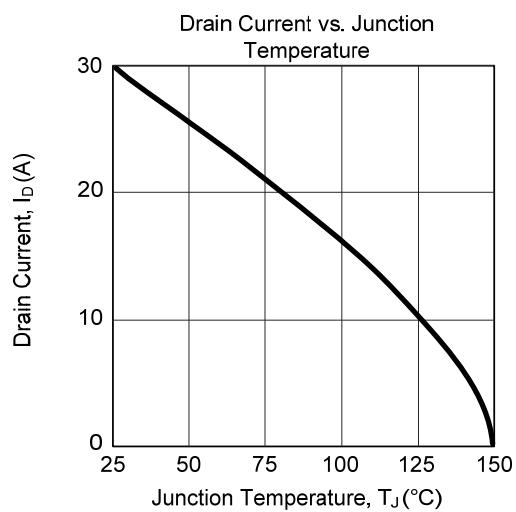
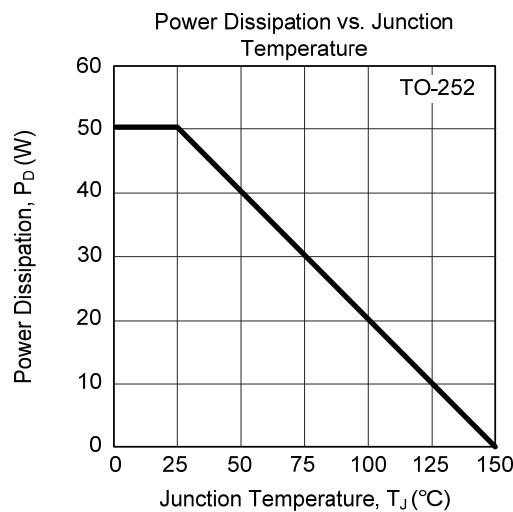
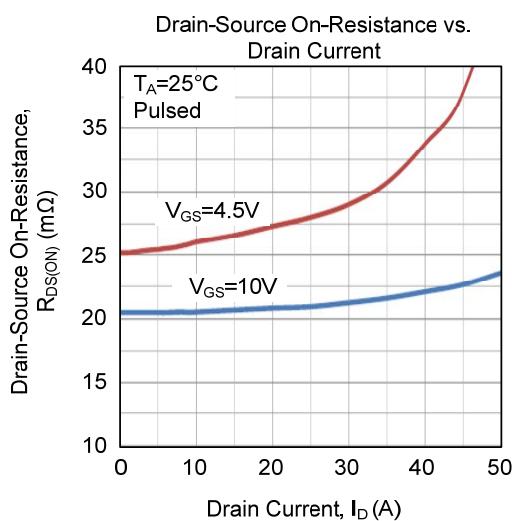
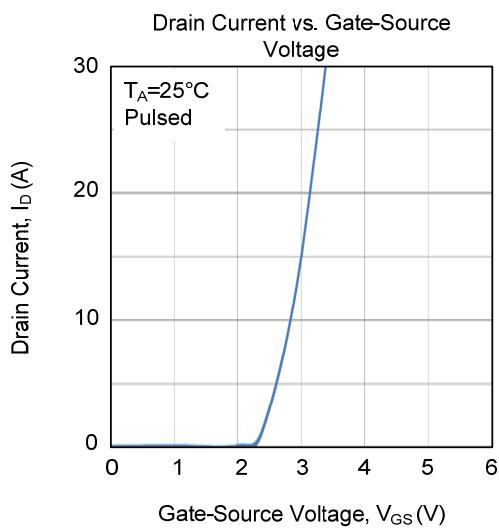
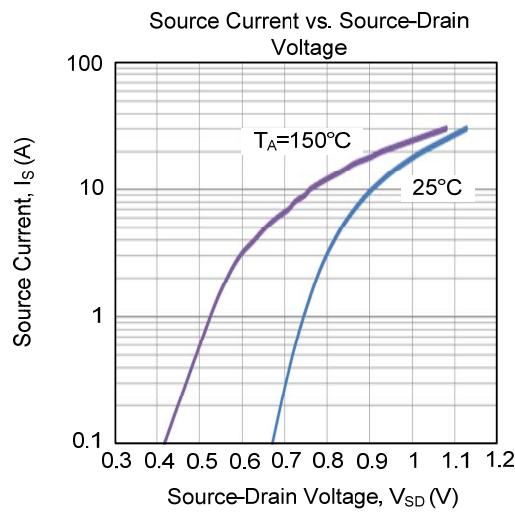
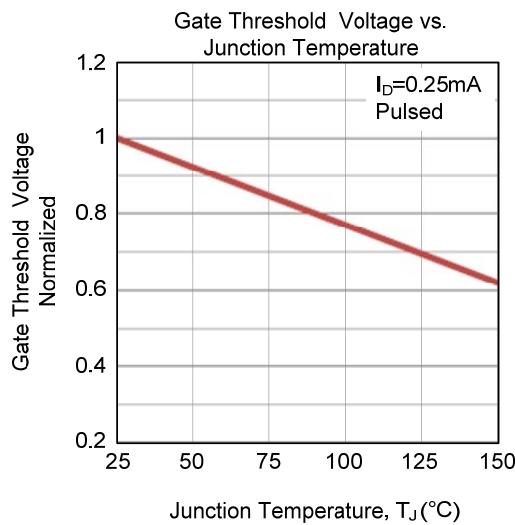


Unclamped Inductive Switching Waveforms

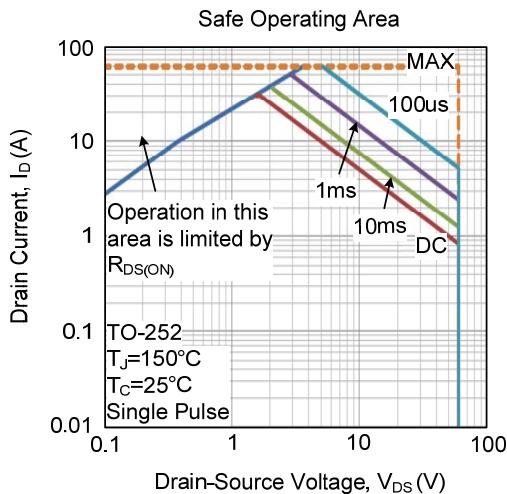
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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